

Form PTO-1449 U.S. Department of Commerce
(REV. 2-82) Patent and Trademark Office

Atty. Docket No.
A35416-PCT-USA
(070050.2721)

Serial No.
10/524,809

**INFORMATION DISCLOSURE STATEMENT
BY APPLICANT**

(Use several sheets if necessary)

Applicant
James S. Im

Filing Date
02/15/2005

Group
2822

Examiner
Not yet assigned

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